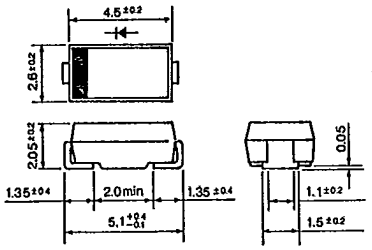
Schottky Barrier Diodes

V_{RM}: 30~90V Io: 0.7~30A

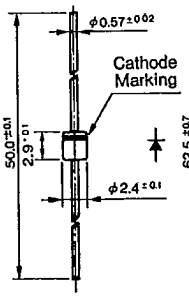
SFPB/AK/EK/RK/FMB/CTB/RBA/RBV

Rating/Characteristics / Type No.	Absolute Maximum Ratings							Electrical Characteristics (Ta=25°C)						Others			
	V_{RSM} (V)	V_{RM}	Io (A)	I_{FSM} (A)	I^2t (A^2S)	Tj (°C)	Tstg (°C)	V_F (V)		I_R (mA)	$I_{R(H)}$ (mA)	trr (μs)		Rth(j-ℓ) (°C/W)	Outline Drawing	Weight(g)	Taping / Note
	Per chip		with Fin	50Hz Half Sine Wave Single Pulse				Max. per chip	I_F (A)	$V_R=V_{RM}$ max (per chip)	$V_R=V_{RM}$, Tj=125°C max (per chip)		I_F/I_{RP} (mA)			
SFPB-54	45	40	1.0	60				0.55	1.0	1.0	50	0.05			⑬	0.072	Available / Surface Mount
SFPB-64	45	40	1.5						2.0								
SFPB-56	60	60	0.7	10				0.62	0.7		7.5	0.1					
SFPB-59	90	90						0.81			5.0						
AK 03	35	30	1.0	25				0.6	1.0		50 (Tj=100°C)				⑭	0.13	
AK 04	45	40															
AK 06	60	60	0.7	10				0.62	0.7		7.5						
AK 09	90	90						0.81			5.0						
EK 03	35	30	1.0	40				0.55	1.5	5.0	50	0.2			⑯	0.3	
EK 04	45	40															
EK 06	60	60	0.7	10				0.62	0.7	1.0	7.5	0.1					
EK 09	90	90						0.81			5.0						
EK 13	35	30	1.5	40				0.55	2.0	5.0	50	0.2			⑰		
EK 14	45	40															
EK 16	60	60		25				0.62	1.5	1.0	15	0.1					
EK 19	90	90		40				0.81		2.0	10						
RK 13	35	30	1.7	60				0.55	2.0	5.0	50	0.2			⑱	0.45	
RK 14	45	40															
RK 16	60	60	1.5	25				0.62	1.5	1.0	15	0.1					
RK 19	90	90		40				0.81		2.0	10						
RK 33	35	30	2.5	50				0.55	2.5	5.0	50	0.1	100/100		⑮	0.6	
RK 34	45	40															
RK 36	60	60	2.0	40				0.62	2.0	2.0	20						
RK 39	90	90		50				0.81		3.0	15						
RK 43	35	30	3.0	80				0.55	3.0	5.0	50				⑲	1.2	For Pulse Rectification
RK 44	45	40															
RK 46	60	60	3.5	70				0.62	3.5	3.0	35						
RK 49	90	90		60				0.81		5.0							
FMB-G14L	45	40	5.0	60	18	−40~		0.55	5.0	5.0	100				⑳	2.1	
FMB-G24H	45	40	10	150	112.5		+125		10	10	65						
FMB-23	35	30	4.0	50					2.0	5.0	35				㉑		
FMB-24	45	40															
FMB-26	60	60		40	8			0.62		1.0	20						
FMB-29	90	90		50	12.5			0.81		3.0	15						
FMB-24M	45	40	6.0	60	18			0.55	3.0	5.0	35				㉑		
FMB-24H	40	40	15	100	50				7.5	7.5	50						
FMB-23L	35	30	10	60					5.0	5.0	35						
FMB-24L	48	40															
FMB-26L	60	60		50	12.5			0.58	4.0	2.5	50						
FMB-29L	90	90	8.0	60	18			0.81		5.0	35						
FMB-33S	35	30	12	75				0.58	6.0	5.0	35				㉒	5.5	
FMB-34S	48	40															
FMB-33	35	30	15	150				0.55	7.5	10	65			2.0			
FMB-34	48	40															
FMB-36	60	60		75	28			0.62		5.0	75						
FMB-39	90	90		100	50			0.81		10	50						
FMB-33M	35	30	30	300				0.55	15	20	100		500/500				
FMB-34M	48	40															
FMB-36M	60	60	20	150	112.5			0.62		10	150		100/100	2.0			
FMB-39M	90	90						0.81	10	15	60						
CTB-24	45	40	4.0	60				0.55	2.0	5	50	0.2			㉓	2.6	
CTB-24L	48	40	10	60					5.0		35	0.1					
CTB-33S	35	30	12	75				0.58	6.0		40				㉔	6.1	
CTB-34S	48	40									35						
CTB-33	35	30	15	150				0.55	10	10	80						
CTB-34	48	40									65						
CTB-33M	35	30	30	300					15	20	100		500/500				
CTB-34M	48	40															
RBA-406B	60	60	4.0	40				0.62	2.0	2.0	20		100/100	5.0	㉕	4.25	

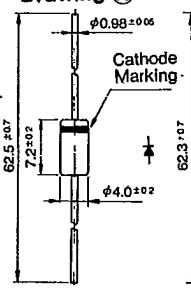
Outline Drawing ⑬



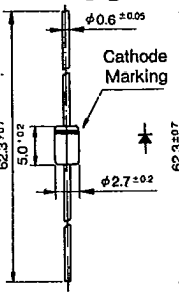
Outline Drawing ⑭



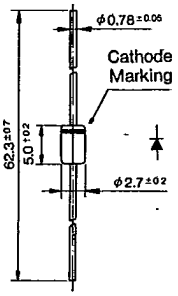
Outline Drawing ⑮



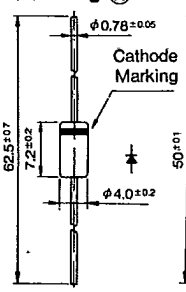
Outline Drawing ⑯



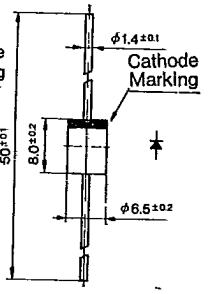
Outline Drawing ⑰



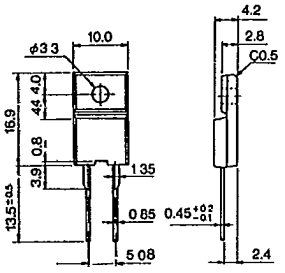
Outline Drawing ⑱



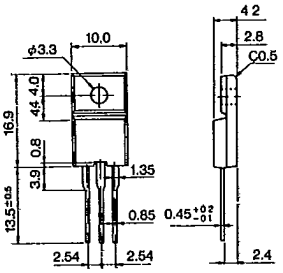
Outline Drawing ⑲



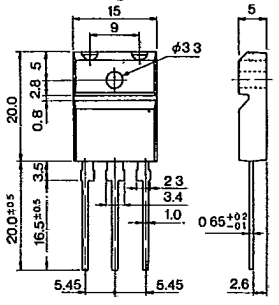
Outline Drawing ⑳



Outline Drawing ㉑



Outline Drawing ㉒



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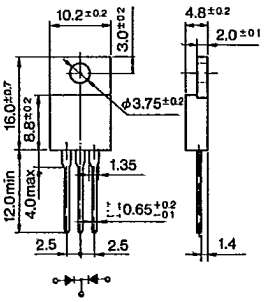
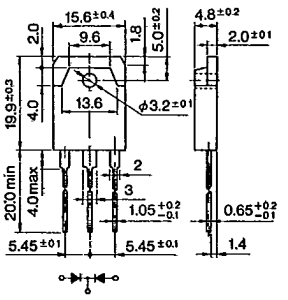
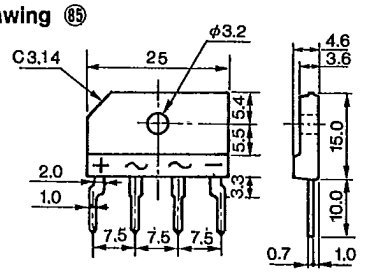


Outline Drawing ㉔



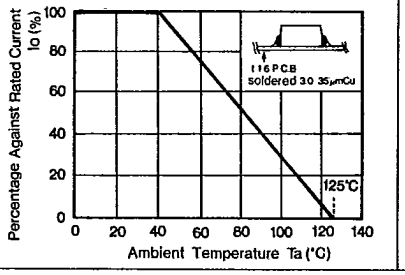
⑬～㉕ Plastic Molded, Flammability : UL94V-0 or Equivalent

Outline Drawing ㉕



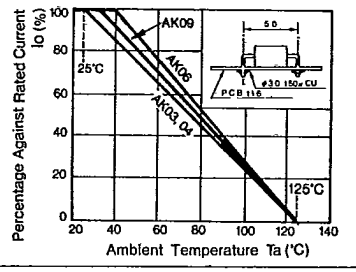
SFPB-54.64.56.59

Io-Ta Deratings



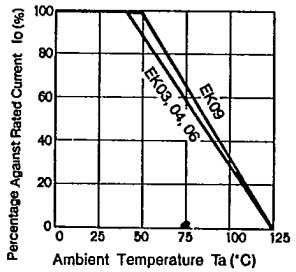
AK 03.04.06.09

Io-Ta Deratings

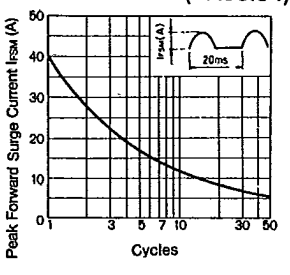


EK 03
EK 04
EK 06
EK 09

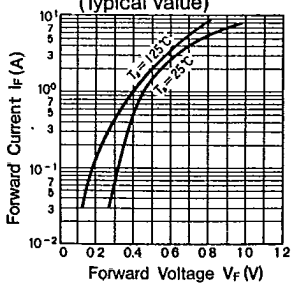
Io-Ta Deratings



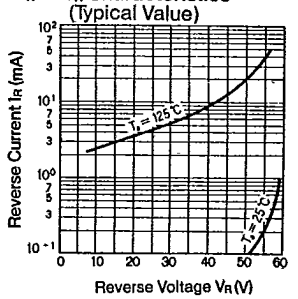
IFSM Characteristics (EK03.04)



IF–VF Characteristics (Typical Value)

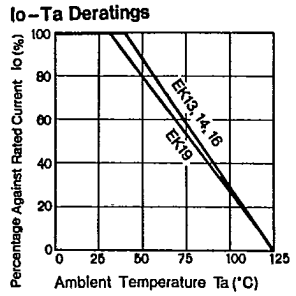


IR – VR Characteristics (Typical Value)

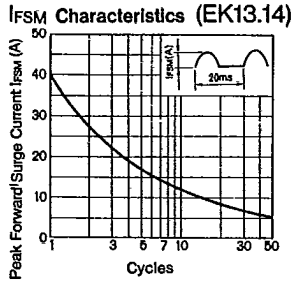


EK 13
EK 14
EK 16
EK 19

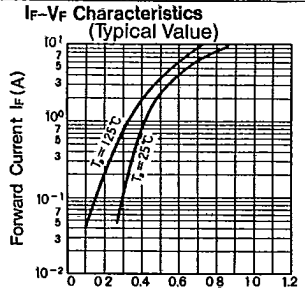
Io-Ta Deratings



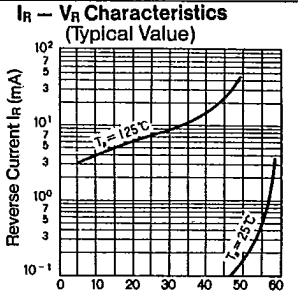
IFSM Characteristics (EK13.14)



IF–VF Characteristics (Typical Value)



IR – VR Characteristics (Typical Value)

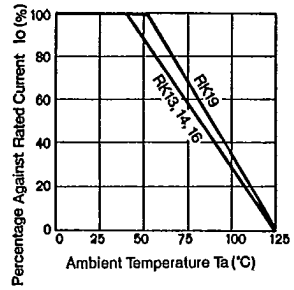


Schottky Barrier Diodes

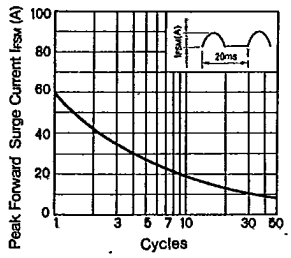
T-23-01

RK 13 RK 14 RK 16 RK 19

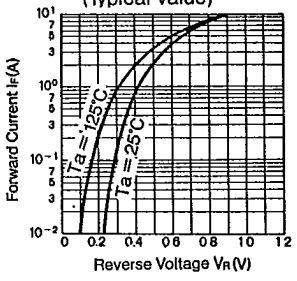
Io–Ta Deratings



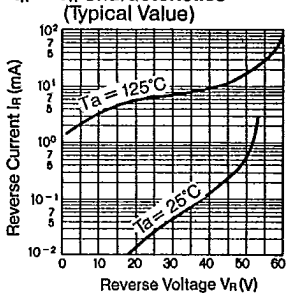
IFSM Characteristics (RK 13, 14)



IF–VF Characteristics (Typical Value)

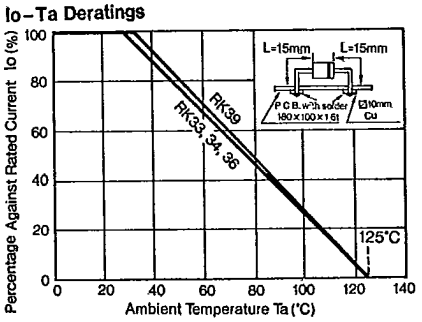


IR – VR Characteristics (Typical Value)



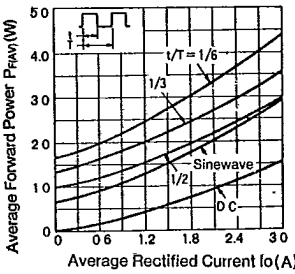
RK 33 RK 34 RK 36 RK 39

Io–Ta Deratings

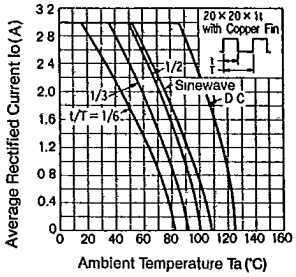


RK 43 RK 44

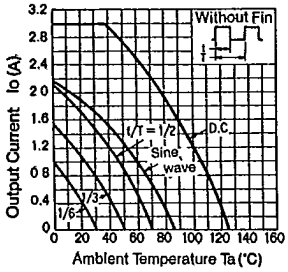
PF(AV) – Io Characteristics (VR = 40V)



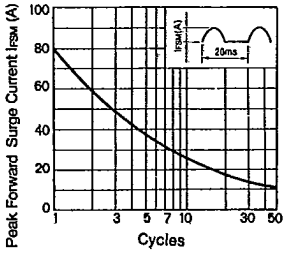
Io–Ta Deratings (VR = 40V)



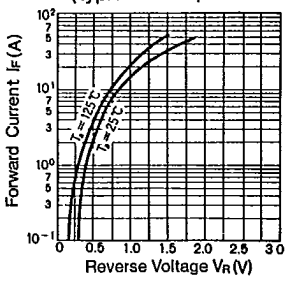
Io–Ta Deratings (VR = 40V)



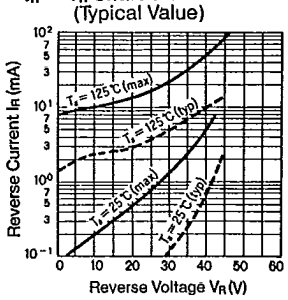
IFSM Characteristics



IF–VF Characteristics (Typical Value)

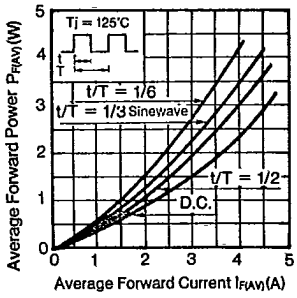


IR – VR Characteristics (Typical Value)

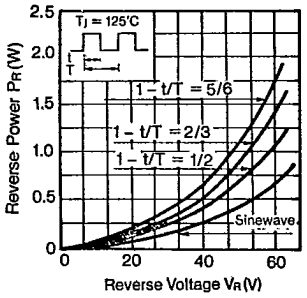


RK 46

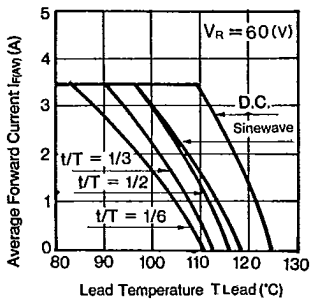
PF(AV)–IF(AV) Characteristics



PR–VR Characteristics

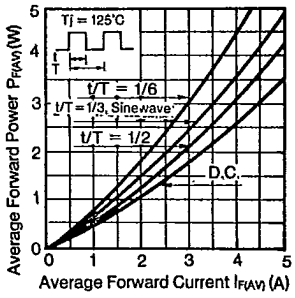


IF(AV)–TLead Characteristics

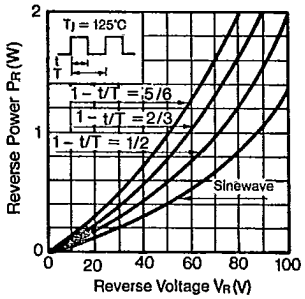


RK 49

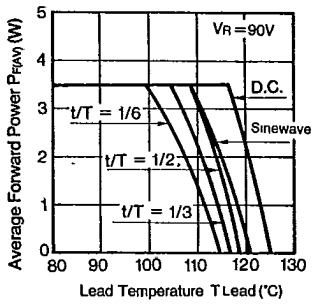
PF(AV)–IF(AV) Characteristics



PR–VR Characteristics

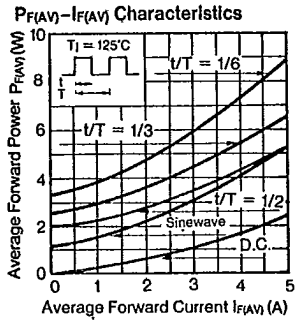


IF(AV)–TLead Characteristics

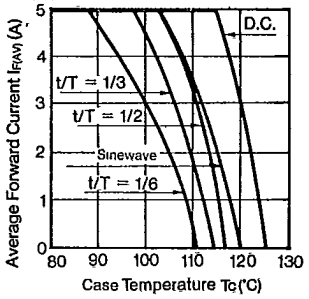


FMB-G14L

$P_{F(AV)}$–$I_{F(AV)}$ Characteristics

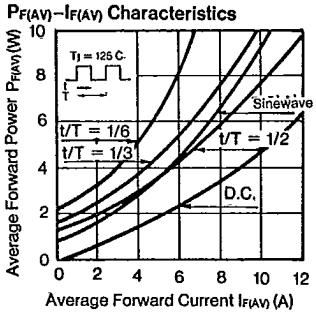


$I_{F(AV)}$–Tc Characteristics

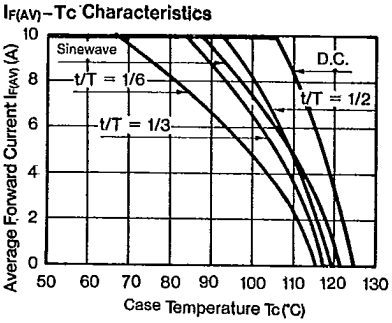


FMB-G24H

$P_{F(AV)}$–$I_{F(AV)}$ Characteristics

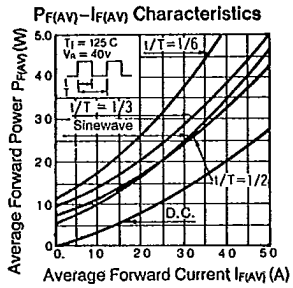


$I_{F(AV)}$–Tc Characteristics

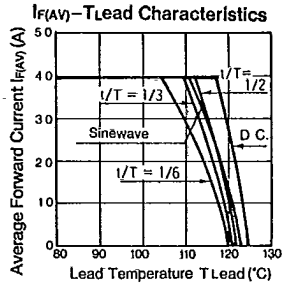


FMB-23
FMB-24

$P_{F(AV)}$–$I_{F(AV)}$ Characteristics

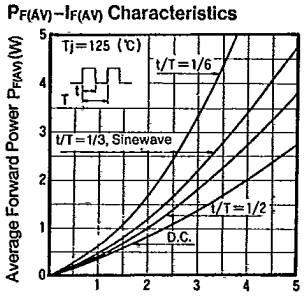


$I_{F(AV)}$–TLead Characteristics

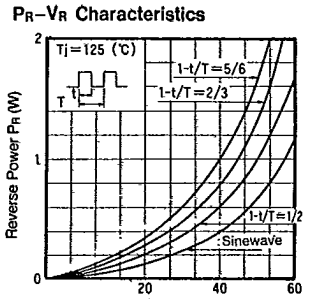


FMB-26

$P_{F(AV)}$–$I_{F(AV)}$ Characteristics

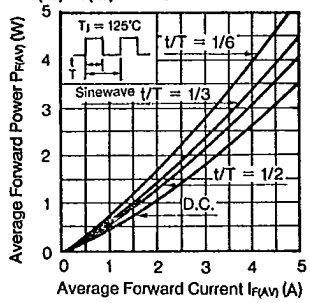


P_R–V_R Characteristics

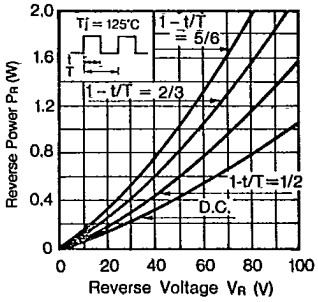


FMB-29

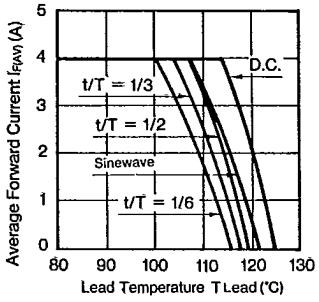
$P_{F(AV)}$–$I_{F(AV)}$ Characteristics



P_R–V_R Characteristics

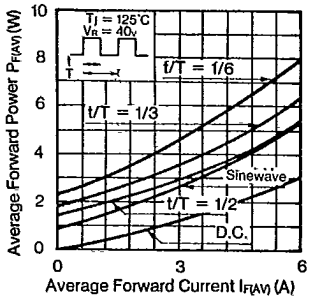


$I_{F(AV)}$–TLead Characteristics



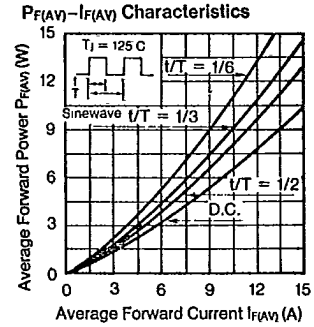
FMB-24M

$P_{F(AV)}$–$I_{F(AV)}$ Characteristics

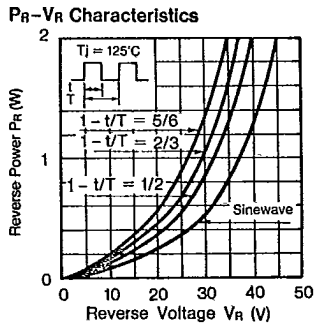


FMB-24H

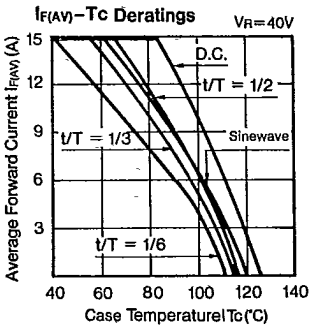
$P_{F(AV)}$–$I_{F(AV)}$ Characteristics



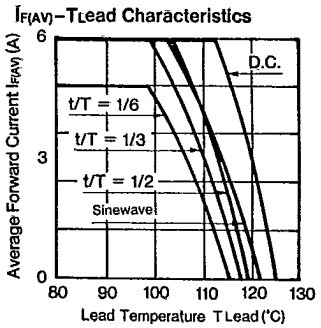
P_R–V_R Characteristics



$I_{F(AV)}$–Tc Deratings V_R=40V

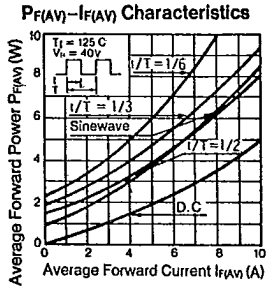


$I_{F(AV)}$–TLead Characteristics

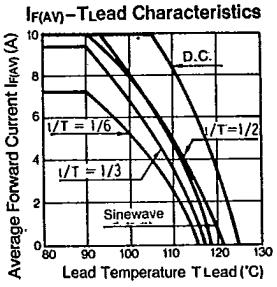


FMB-23L
FMB-24L

$P_{F(AV)}$–$I_{F(AV)}$ Characteristics

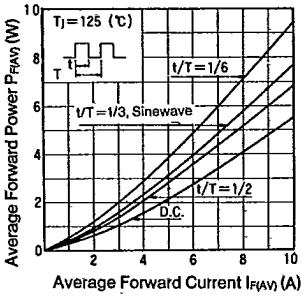


$I_{F(AV)}$–TLead Characteristics

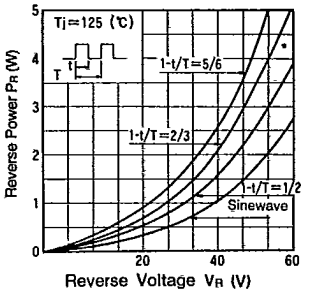


FMB-26L

$P_{F(AV)}$–$I_{F(AV)}$ Characteristics



P_R–V_R Characteristics



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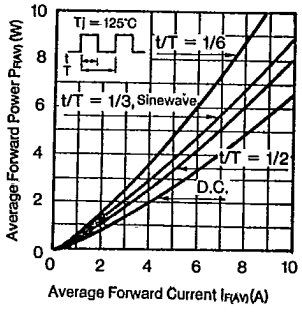
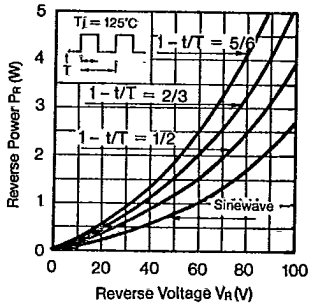
FMB-29L

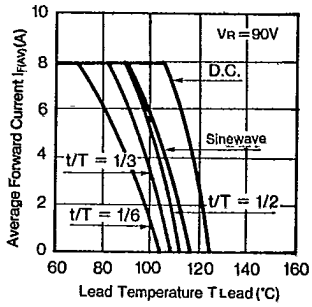
$P_{F(AV)} - I_{F(AV)}$ Characteristics



$P_R - V_R$ Characteristics

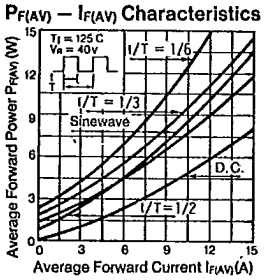


$I_{F(AV)} - T_{Lead}$ Characteristics

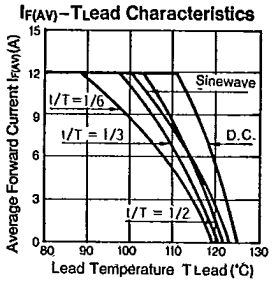


FMB-33S
FMB-34S

$P_{F(AV)} - I_{F(AV)}$ Characteristics

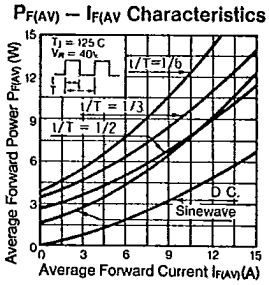


$I_{F(AV)} - T_{Lead}$ Characteristics

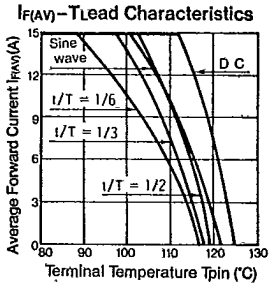


FMB-33
FMB-34

$P_{F(AV)} - I_{F(AV}$ Characteristics

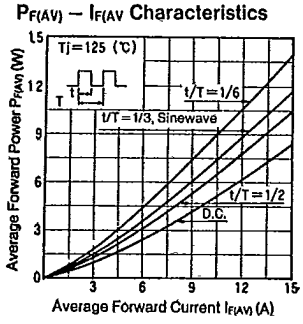


$I_{F(AV)} - T_{Lead}$ Characteristics

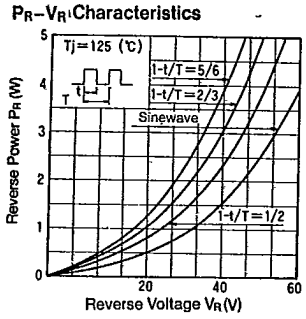


FMB-36

$P_{F(AV)} - I_{F(AV}$ Characteristics

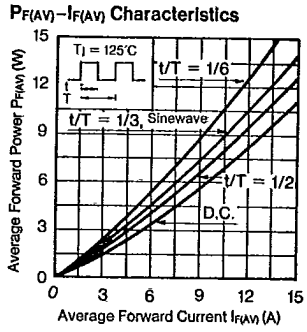


$P_R - V_R$ Characteristics

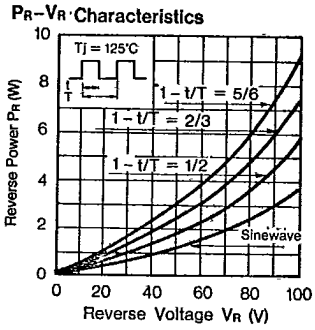


FMB-39

$P_{F(AV)} - I_{F(AV)}$ Characteristics

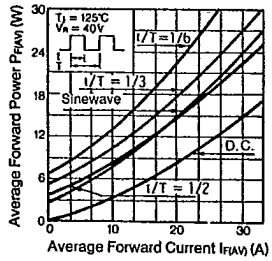


$P_R - V_R$ Characteristics

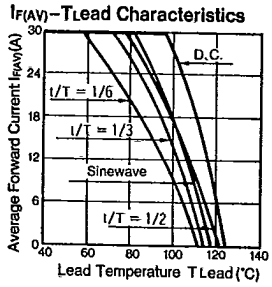


FMB-33M
FMB-34M

$P_{F(AV)} - I_{F(AV)}$ Characteristics

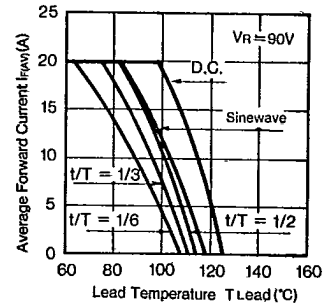


$I_{F(AV)} - T_{Lead}$ Characteristics



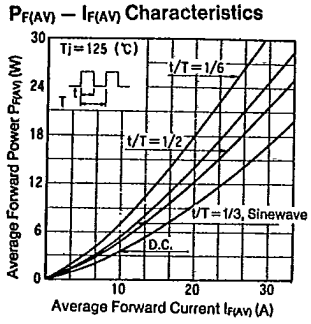
FMB-39M

$I_{F(AV)} - T_{Lead}$ Characteristics

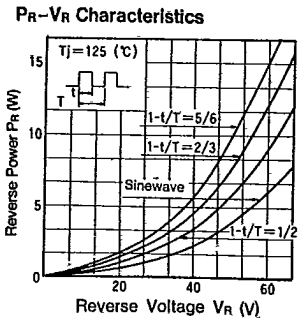


FMB-36M

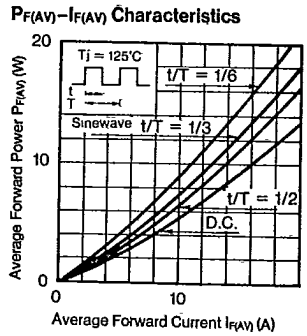
$P_{F(AV)} - I_{F(AV)}$ Characteristics



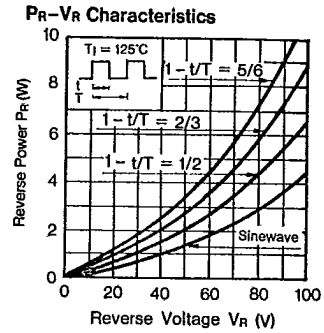
$P_R - V_R$ Characteristics



$P_{F(AV)} - I_{F(AV)}$ Characteristics



$P_R - V_R$ Characteristics



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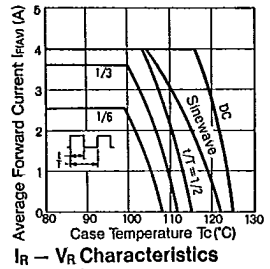
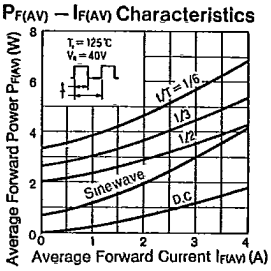
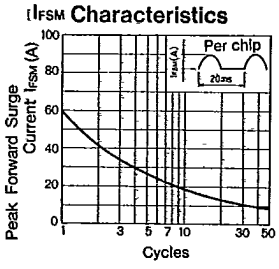
$I_{F(AV)}$ – Tc Deratings



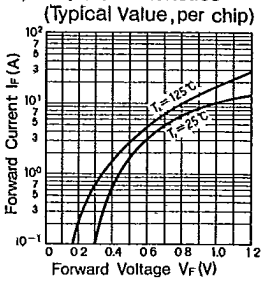
$P_{F(AV)}$ – $I_{F(AV)}$ Characteristics



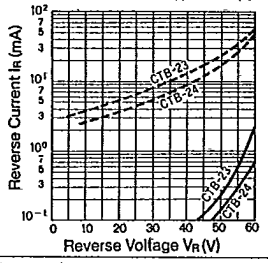
I_{FSM} Characteristics



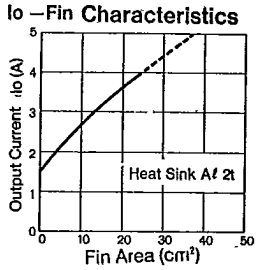
I_F – V_F Characteristics (Typical Value, per chip)



I_R – V_R Characteristics (Typical Value, per chip)

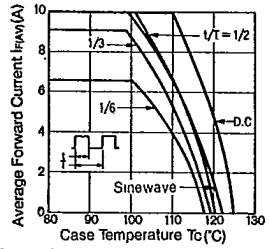


Io – Fin Characteristics

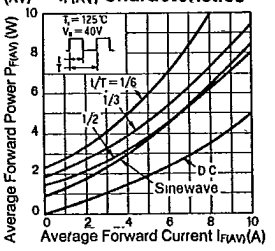


CTB-24L

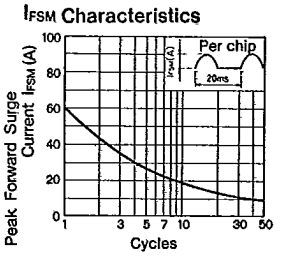
$I_{F(AV)}$ – Tc Deratings



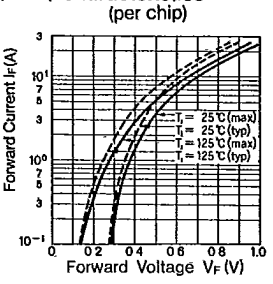
$P_{F(AV)}$ – $I_{F(AV)}$ Characteristics



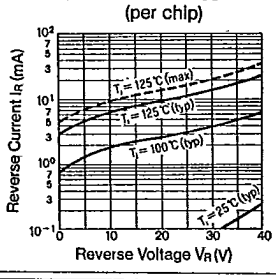
I_{FSM} Characteristics



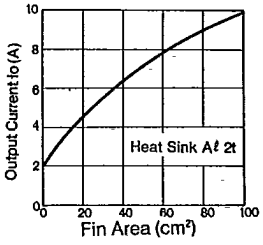
I_F – V_F Characteristics (per chip)



I_R – V_R Characteristics (per chip)

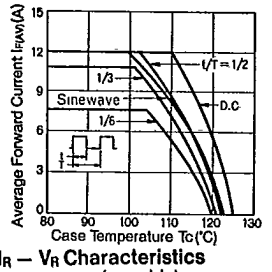


Io – Fin Characteristics

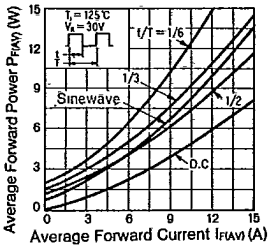


CTB-33S

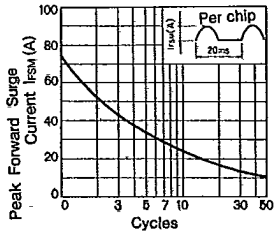
$I_{F(AV)}$ – Tc Deratings



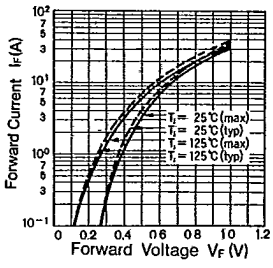
$P_{F(AV)}$ – $I_{F(AV)}$ Characteristics



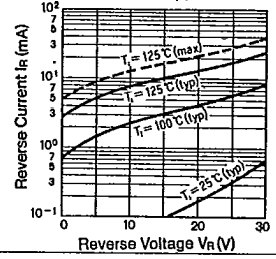
I_{FSM} Characteristics



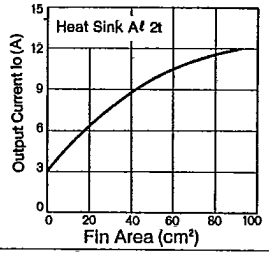
I_F – V_F Characteristics (per chip)



I_R – V_R Characteristics (per chip)



Io – Fin Characteristics



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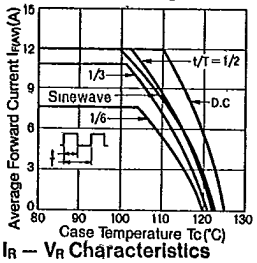
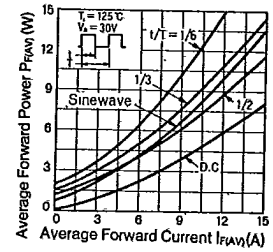
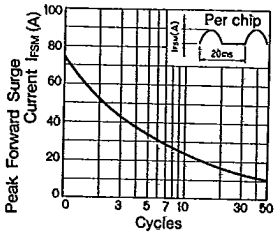
$I_{F(AV)}$ – Tc Deratings



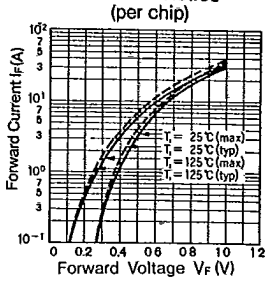
$P_{F(AV)}$ – $I_{F(AV)}$ Characteristics



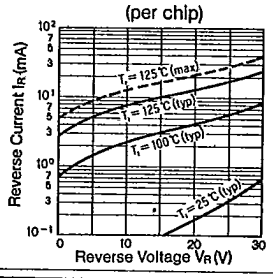
I_{FSM} Characteristics



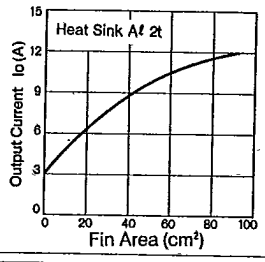
I_F – V_F Characteristics (per chip)



I_R – V_R Characteristics (per chip)

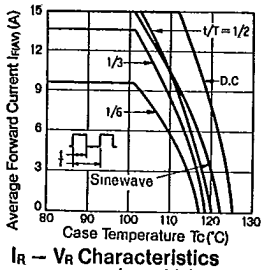


Io –Fin Characteristics

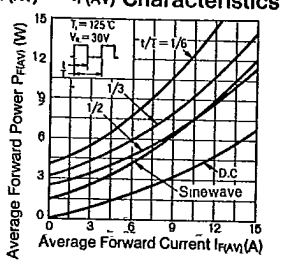


CTB-33 Series

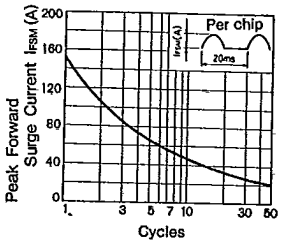
$I_{F(AV)}$ – Tc Deratings



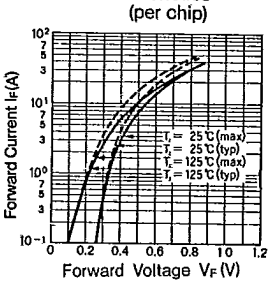
$P_{F(AV)}$ – $I_{F(AV)}$ Characteristics



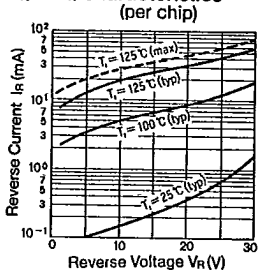
I_{FSM} Characteristics



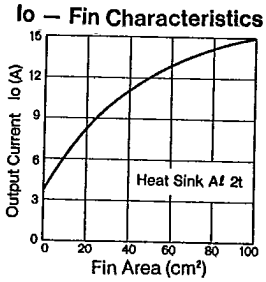
I_F–V_F Characteristics (per chip)



I_R – V_R Characteristics (per chip)

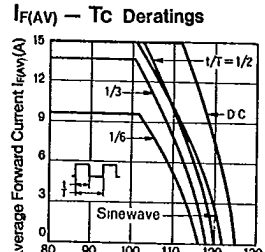


Io – Fin Characteristics

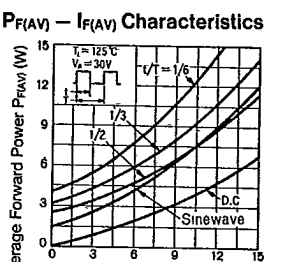


CTB-34

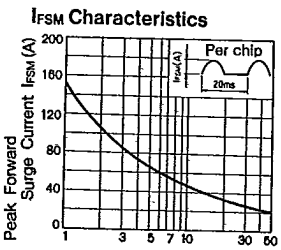
$I_{F(AV)}$ – Tc Deratings



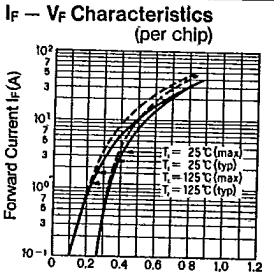
$P_{F(AV)}$ – $I_{F(AV)}$ Characteristics



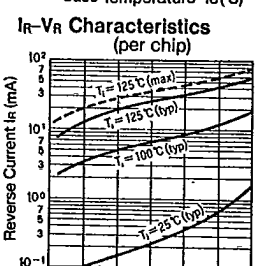
I_{FSM} Characteristics



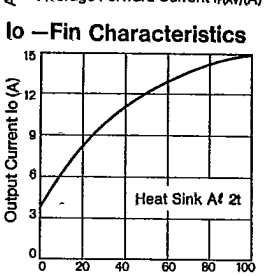
I_F – V_F Characteristics (per chip)



I_R–V_R Characteristics (per chip)



Io –Fin Characteristics

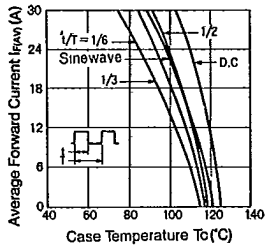


Characteristics

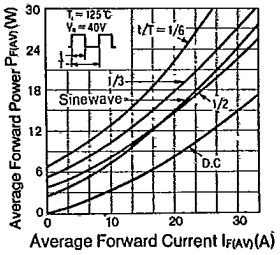
T-23-01

CTB-33M
CTB-34M

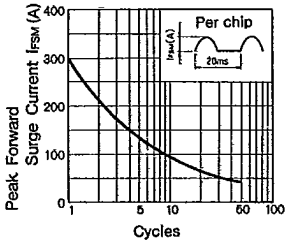
$I_{F(AV)}$ — Tc Deratings



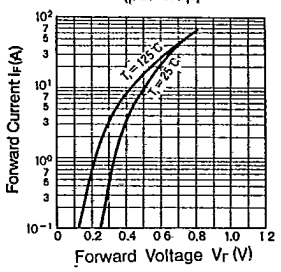
$P_{F(AV)}$ — $I_{F(AV)}$ Characteristics



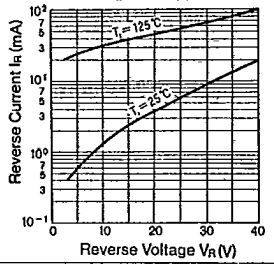
I_{FSM} Characteristics



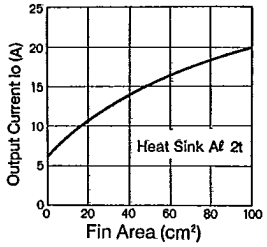
I_F — V_F Characteristics (per chip)



I_R — V_R Characteristics (per chip)



Io —Fin Characteristics



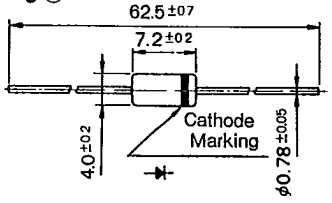
Avalanche Diodes

■ V_{RM}: 40~400V ■ I_{ZSM}: 0.1~3.0A

RM/R /RY

Rating/ Characteristics	Absolute Maximum Ratings				Electrical Characteristics (Ta=25°C)						Others			
Type No.	V_{RM} (V)	I_{ZSM} (A)	Tj (°C)	Tstg (°C)	V_Z (V)	I_R (μA)	$I_{R(H)}$ (μA)	J (V/°C)	γ_Z (%/°C)	R_Z (Ω)	Outline Drawing	Weight(g)	Taping	Application
		Square Wave Single Pulse			Iz=1mA Instantaneous	$V_R=V_{RM}$	$V_R=V_{RM}$	Iz=1mA	Iz=1mA	Iz=0.5~1.5A				
RM 25	40	3.0	−40~+130		50~61.5	5.0	20 (Ta=80°C)	—	0.09typ.	5 max	⑧⑥	0.44	Available	For Surge Absorption
RM 26	50				60~70									
R 2M	130	1.0(100μs)	−40~+150		135~180	10	50(Ta=100°C)	+0.15typ.	—	—		0.44		
RY 23	200	0.1(100μs)	−40~+150		250~400		50 (Ta=80°C)		—	—		0.44		
RY 24	400				400~450									

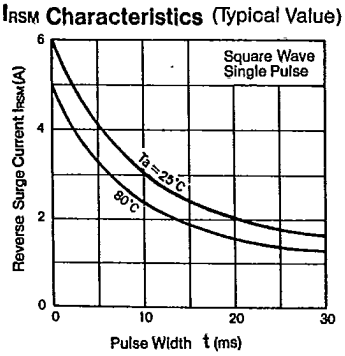
Outline Drawing ⑧⑥



⑧⑥ Plastic Molded, Flammability : UL94V-0 or Equivalent

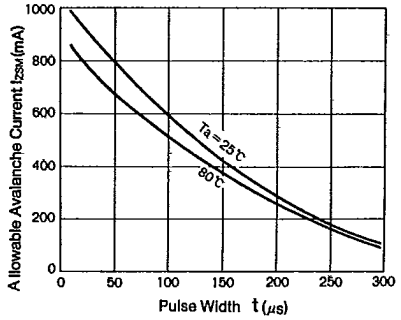
RM 25
RM 26

I_{RSM} Characteristics (Typical Value)



RY 23

I_{ZSM} Characteristics (Typical Value)



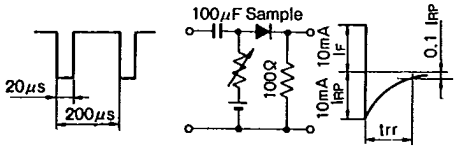
Symbols/trr Measurement Circuit

Symbols

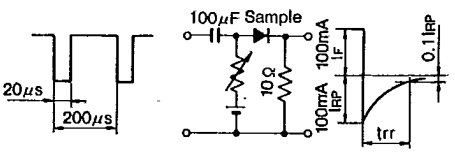
V_{RSM}	Peak Reverse Surge Voltage	I_{RSM}	Peak Reverse Surge Current	Tstg	Storage Temperature
V_{RM}	Peak Reverse Voltage	I_R	Reverse Current	trr	Reverse Recovery Time
V_{P-P}	Reverse Voltage (Peak to Peak)	I_{RP}	Peak Reverse Current	Ct	Total Capacitance Between Terminals
V_R	Reverse Voltage	$I_{R(H)}$	Reverse Current (High Temperature)	Rth(j-c)	Thermal Resistance, Junction to Case
V_F	Forward Voltage	Iz	Avalanche Current	rz	Temperature Coefficient of Breakdown Voltage
V_B	Breakdown Voltage	I_{ZSM}	Allowable Avalanche Current	Rz	Equivalent Resistance of Breakdown Region
I_O	Average Rectified Forward Current	Ta	Ambient Temperature	$P_{F(AV)}$	Average Forward Power Dissipation
I_F	Forward Current	Tj	Junction Temperature	I^2t	I^2t limiting Value
$I_{F(AV)}$	Average Forward Current	Topr	Operating Ambient Temperature		
I_{FSM}	Peak Forward Surge Current	Tc	Case Temperature		

Reverse Recovery Time Measurement Circuit

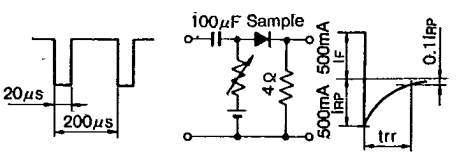
① $I_F = I_{RP} = 10mA$ to $1mA$



② $I_F = I_{RP} = 100mA$ to $10mA$

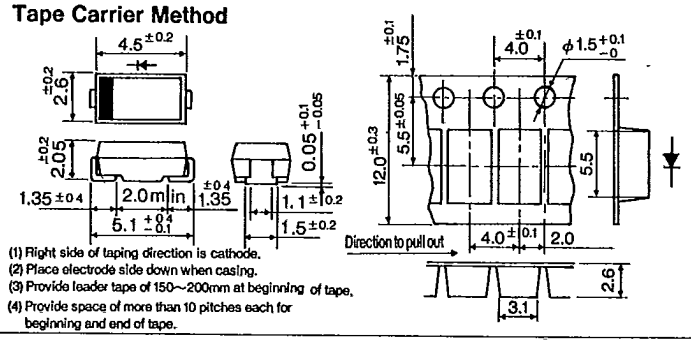
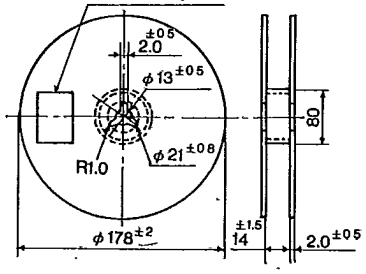
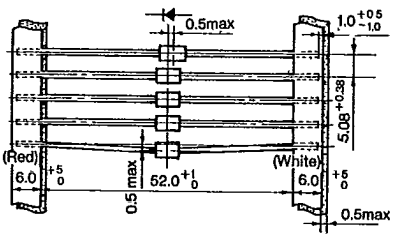
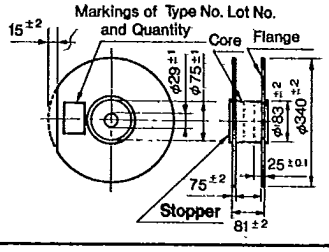


③ $I_F = I_{RP} = 500mA$ to $50mA$

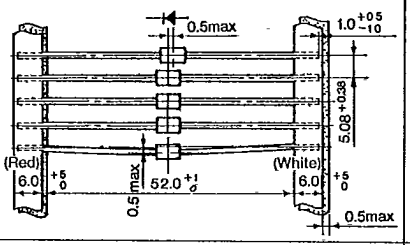
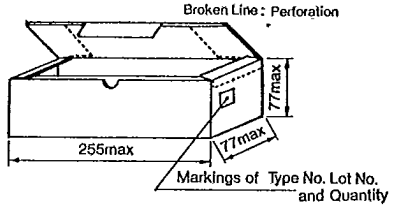
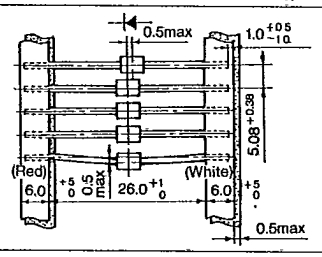
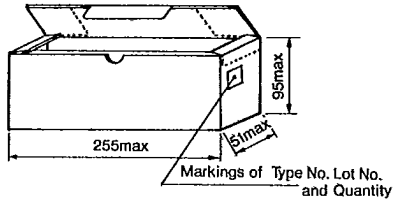
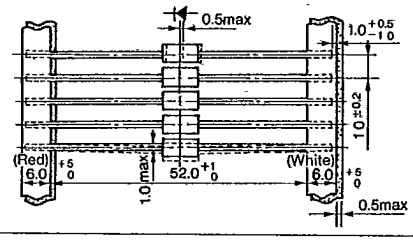
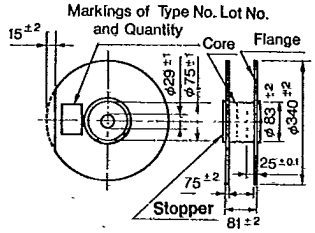
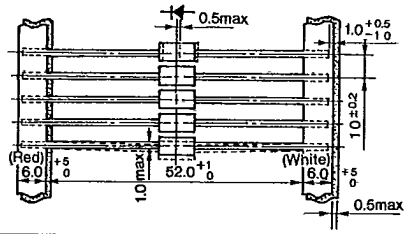
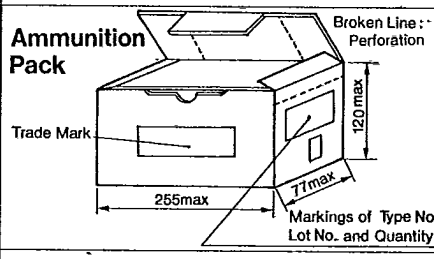
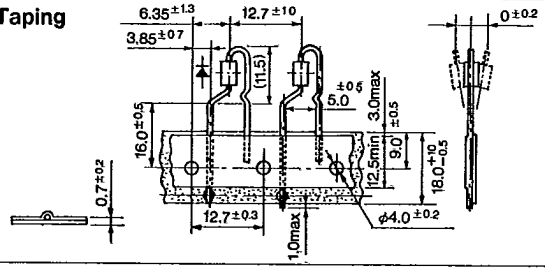
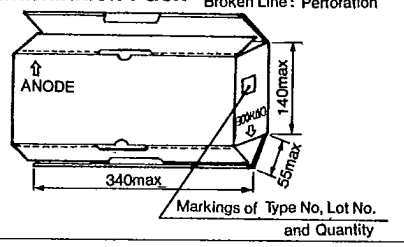
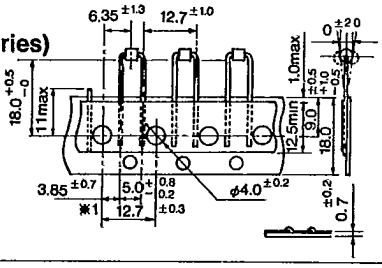
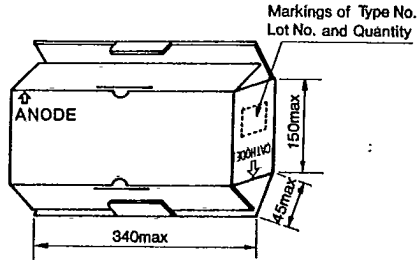
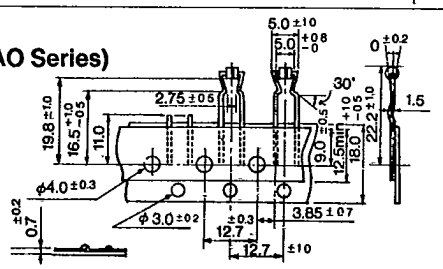


Taping Specifications

Excluding High Voltage Diodes

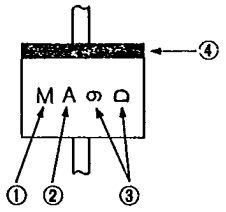
Designation	Dimension (in mm)	Packaging Dimension and Marking	Quantity
V Add Suffix [V] to Type No.	**Tape Carrier Method**  (1) Right side of taping direction is cathode. (2) Place electrode side down when casing. (3) Provide leader tape of 150~200mm at beginning of tape. (4) Provide space of more than 10 pitches each for beginning and end of tape.	**Reel** Marking of Type No., Lot No. and Quantity 	1,800 pcs per reel
V Add Suffix [V] to type No.	**Axial Taping** 	**Reel** Markings of Type No. Lot No. and Quantity 	5,000 pcs per reel (2.7φ body) 3,000 pcs per reel (4.0φ body)

Taping Specifications

Designation	Dimension (in mm)	Packaging Dimension and Marking	Quantity
V1 Add Suffix [V1] to Type No.	Axial Taping 	Ammunition Pack 	2,000 pcs per box (2.7φ body) 1,000 pcs per box (4.0φ body)
VO Add Suffix [VO] to Type No.	Axial Taping 	Ammunition Pack 	2,000 pcs per box (2.7φ body) (2.4φ body)
V3 Add Suffix [V3] to Type No.	Axial Taping 	Reel 	1,500 pcs per reel (5.2φ body)
V4 Add Suffix [V4] to Type No.	Axial Taping 	Ammunition Pack 	1,000 pcs per box (5.2φ body)
W Add Suffix [W] to Type No.	Radial Taping 	Ammunition Pack 	4,000 pcs per box (2.7φ body) (0.6φ lead)
WS Add Suffix [WS] to Type No.	Radial Taping (Applicable to AO Series) 	Ammunition Pack 	2,500 pcs per box (2.4φ body)
WK Add Suffix [WK] to Type No.	Radial Taping (Applicable to AO Series) 		2,500 pcs per box (2.4φ body)

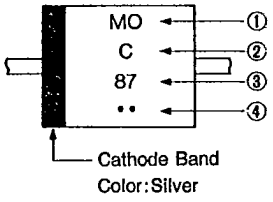
Marking Guide

1 Small TMD



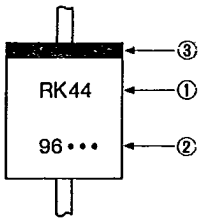
①Type Designation (in abbreviation)
AM01 is abbreviated as M.
②Class Designation
Z:200V, No Letter:400V, A:600V
③A:Year (Last Number of AD Year)
B:Month (Jan. to Sept. are represented by numbers 1 to 9 respectively, and Oct., Nov., and Dec. are abbreviated as O, N and D respectively)
④Cathode Band:Successive Band, however AU02 Type is Non-Successive Band.

2 E/EO Type TMD



①Type Designation (in abbreviation)
EM01 is abbreviated as MO, EM2 is abbreviated as M2.
②Class Designation
Z:200V, No Letter:400V, A:600V
B:800 V, C:1000V, F:1500V
However, EU02A to be marked 2A, and EU2YX to be marked Y.
③Abbreviations Representing Production Period
A:Year (Last Number of AD Year)
B:Month (1~9, 0, N, D)
④Production Period Divided in 3 ten day terms
• : 1st 10days •• : 2nd 10days ••• : 3rd 10days

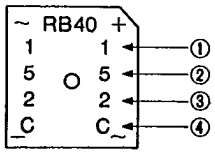
3 R Type TMD



①Type Designation:Mark in 2 sets
②Production Period:Mark in 4 sets
A:Year (Last Number of AD Year)
B:Month (1~9, 0, N, D)
③Production Period Divided in 3 ten day terms
• : 1st 10days •• : 2nd 10days ••• : 3rd 10days
④Cathode Band Color:Silver:For Power Supply
Yellow: For Middle Speed
Red : For High Speed and Ultra-High Speed

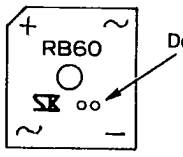
4 RB40/60

(RB40 Series)



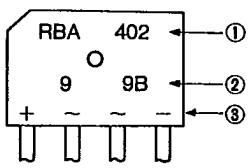
①Peak Reverse Voltage Designation
1, 2, 4, 6, C
Production Period
②Year (Last Number of AD Year)
③Month (1~9, 0, N, D)
④Divided in 3 ten day terms
A:1st 10days, B:2nd 10days
C:3rd 10days
Color Designation: Silver

(RB60 Series)



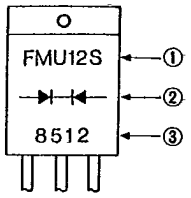
Dot Designation RB601 Violet
RB602 No Color
RB604 Blue
RB606 White

5 RBV/RBA



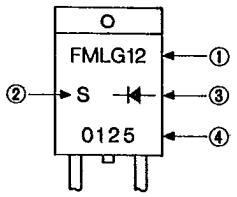
①Type Designation
②Lot Number
1st : Year (Last Number of AD Year)
2nd: Month (1~9, 0, N, D)
3rd : Divided 1~3 ten day Terms
A:1st 10 days B:2nd 10 days
C:3rd 10 days
③In-Put Designation

6 TO220 Type (FM or CT Type)



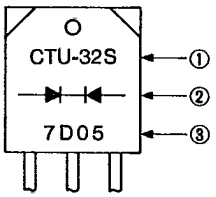
①Type Designation
Show FMU-12S as FMU12S.
②Polarity:Rectifier Symbols
③Lot Number (Laser Marking)
1st : Year (Last Number of AD Year)
2nd : Month (0~9, 0, N, D)
3rd, 4th: Day

7 TO220 Type (FM or CT Type, single chip)



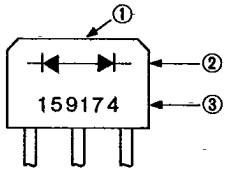
①Type Designation:Omit Last Letter
Show FML-G12S as FMLG12.
②Last Letter of Type Designation
③Polarity:Recitifier Symbols
④Lot Number (Laser Marking)
1st : Year (Last Number of AD Year)
2nd : Month (0~9, 0, N, D)
3rd, 4th: Day

8 TO3P Type (FM or CT Type)



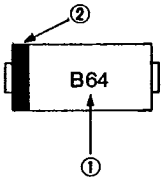
①Type shown in full designation
However, CTB-34/34S/34M are marked as CTB-34, CTU-G3DR is marked as CTUG3DR.
②Polarity:Rectifier Symbols
③Lot Number:
1) M, U, G and L Types
First Number : Last Digit of AD Year
Second Number : Month
Third and Fourth Numbers:Day
Fifth Number : None
2) For types CTB-34/34S/34M, the fifth letter shows type designation. If no fifth number, the type is CTB-33 or CTB-34.
3) Marking Color:Silver

9 MI-10/15 Type



①MI-10/15 is die-stamped on the top of the case.
②Rectifier Symbols
③Lot Number:
First Number (Letter) :Peak Reverse Voltage:
0=50V, 1=100V, 2=200V,
4=400V, 6=600V, C=1000V
Second Number :Last Digit of AD Year
Third Number :Month
Fourth and Fifth Numbers:Day
Sixth Number :Production number and
U:Voltage Doubler Type

10 SFP Type



①Type Designation:
SFPB-64 is abbreviated at B64.
②Cathode Band